

L Number	Hits	Search Text	DB	Time stamp
1	236	DRAM adj bit adj lines	USPAT	2003/04/13 12:52
2	0	(DRAM adj bit adj lines) and (chem-mech adj polishing) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and (active adj region) and opening and etchable	USPAT	2003/04/13 12:55
3	0	(DRAM adj bit adj lines) and (chem-mech adj polishing) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and (active adj region) and opening	USPAT	2003/04/13 12:58
4	0	(DRAM adj bit adj lines) and (chem-mech adj polishing) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and active and region and opening	USPAT	2003/04/13 12:56
5	2	(DRAM adj bit adj lines) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and active and region and opening	USPAT	2003/04/13 13:07
6	1	(DRAM adj bit adj lines) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and (active adj region) and opening and polishing	USPAT	2003/04/13 12:59
7	2	((DRAM adj bit adj lines) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and active and region and opening) and (polishing or mechanical or chemical or opening or hole or etch or etching or etchable or conductive or lines or bit or word or line or source or drain or memory or material or structure or substrate oe entire or trench or STI)	USPAT	2003/04/13 13:03
8	2	((DRAM adj bit adj lines) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and active and region and opening) and (polishing or mechanical or chemical or opening or hole or etch or etching or etchable or conductive or lines or bit or word or line or source or drain or memory or material or structure or substrate oe entire or trench or STI or silicon or nitride or oxide)	USPAT	2003/04/13 13:39
9	4	(DRAM adj bit adj lines) and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and word and line and gate and active and region	USPAT	2003/04/13 13:27
10	1		USPAT	2003/04/13 13:26
11	1		USPAT	2003/04/13 13:26
12	1		USPAT	2003/04/13 13:26
13	1		USPAT	2003/04/13 13:26
14	1		USPAT	2003/04/13 13:27
15	17	DRAM and STI and (first adj insulating) and (second adj insulating) and (third adj insulating) and (fourth adj insulating) and word and line and gate and active and bit	USPAT	2003/04/13 13:38
16	1	("6475858").PN.	USPAT	2003/04/13 13:39
17	1	(("6475858").PN.) and (polishing or mechanical or chemical or opening or hole or etch or etching or etchable or conductive or lines or bit or word or line or source or drain or memory or material or structure or substrate oe entire or trench or STI or silicon or nitride or oxide)	USPAT	2003/04/13 13:51
18	1		USPAT	2003/04/13 13:50
19	1		USPAT	2003/04/13 13:50
20	1		USPAT	2003/04/13 13:50
21	1		USPAT	2003/04/13 13:51
22	1		USPAT	2003/04/13 13:51
23	1		USPAT	2003/04/13 13:51
24	1	("5893734").PN.	USPAT	2003/04/13 13:52
25	1	("5400275").PN.	USPAT	2003/04/13 13:53
26	1	("5895239").PN.	USPAT	2003/04/13 13:53
27	1	("6083790").PN.	USPAT	2003/04/13 13:53
28	861	438/381	USPAT	2003/04/13 13:54
29	899	438/241	USPAT	2003/04/13 13:54
30	248	438/242	USPAT	2003/04/13 13:54
31	708	438/270	USPAT	2003/04/13 13:54
32	782	438/680	USPAT	2003/04/13 13:54